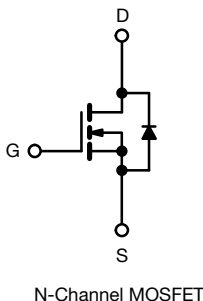
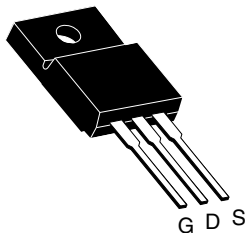


D Series Power MOSFET

TO-220 FULLPAK


N-Channel MOSFET

FEATURES

- Optimal design
 - Low area specific on-resistance
 - Low input capacitance (C_{iss})
 - Reduced capacitive switching losses
 - High body diode ruggedness
 - Avalanche energy rated (UIS)
- Optimal efficiency and operation
 - Low cost
 - Simple gate drive circuitry
 - Low figure-of-merit (FOM): $R_{on} \times Q_g$
 - Fast switching
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS*
Available

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

APPLICATIONS

- Consumer electronics
 - Displays (LCD or Plasma TV)
- Server and telecom power supplies
 - SMPS
- Industrial
 - Welding
 - Induction heating
 - Motor drives
- Battery chargers

PRODUCT SUMMARY

V_{DS} (V) at T_J max.	550	
$R_{DS(on)}$ max. (Ω) at 25 °C	$V_{GS} = 10$ V	0.28
Q_g max. (nC)	76	
Q_{gs} (nC)	11	
Q_{gd} (nC)	17	
Configuration	Single	

ORDERING INFORMATION

Package	TO-220 FULLPAK
Lead (Pb)-free	SiHF18N50D-E3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	500	V
Gate-source voltage	V_{GS}	± 30	
Gate-source voltage AC ($f > 1$ Hz)		30	
Continuous drain current ($T_J = 150$ °C) ^e	V_{GS} at 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed drain current ^a	I_{DM}	53	
Linear derating factor		0.3	W/°C
Single pulse avalanche energy ^b	E_{AS}	115	mJ
Maximum power dissipation	P_D	39	W
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	°C
Drain-source voltage slope	dV/dt	24	V/ns
Reverse diode dV/dt ^d		0.4	
Soldering recommendations (peak temperature) ^c	For 10 s	300	°C
Mounting torque	M3 screw	0.6	Nm

Notes

- Repetitive rating; pulse width limited by maximum junction temperature
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 2.3$ mH, $R_g = 25$ Ω , $I_{AS} = 10$ A
- 1.6 mm from case
- $I_{SD} \leq I_D$, starting $T_J = 25$ °C
- Limited by maximum junction temperature

**THERMAL RESISTANCE RATINGS**

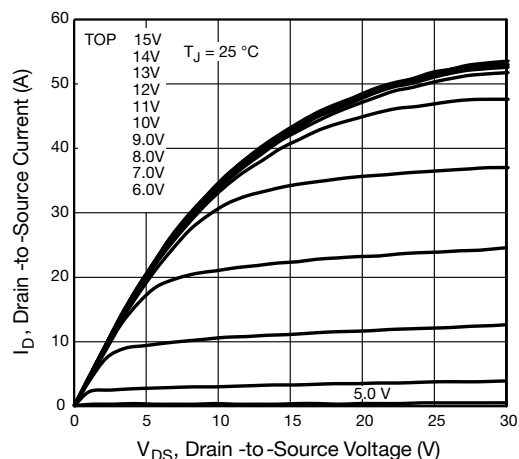
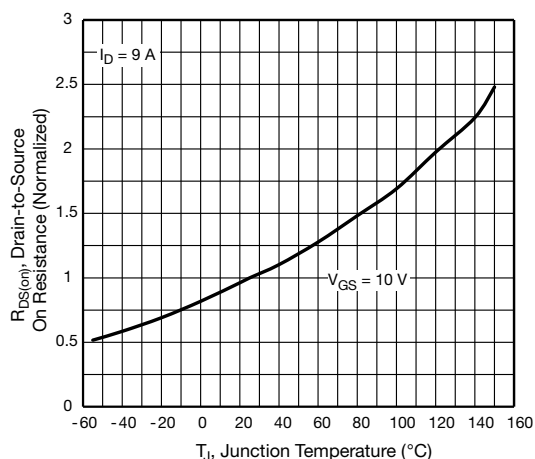
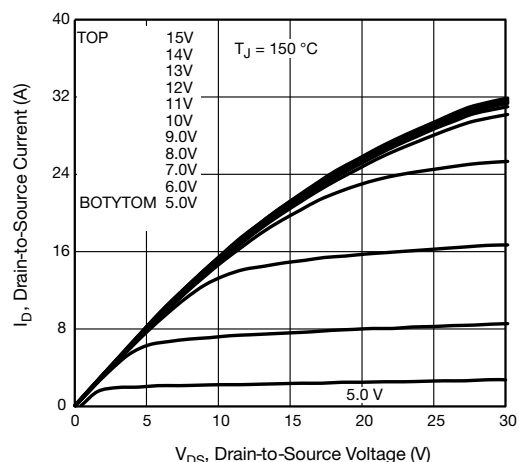
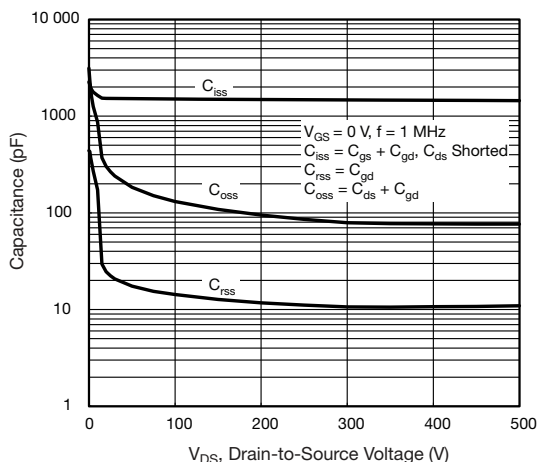
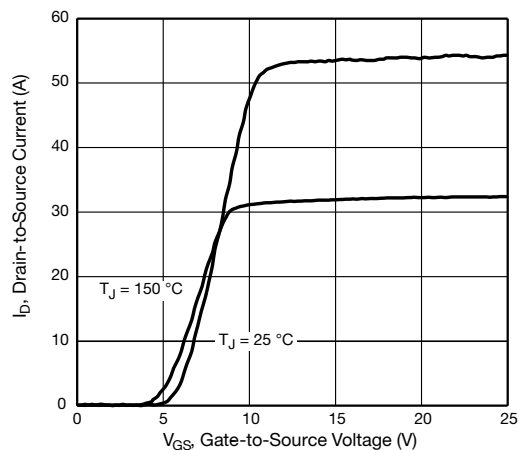
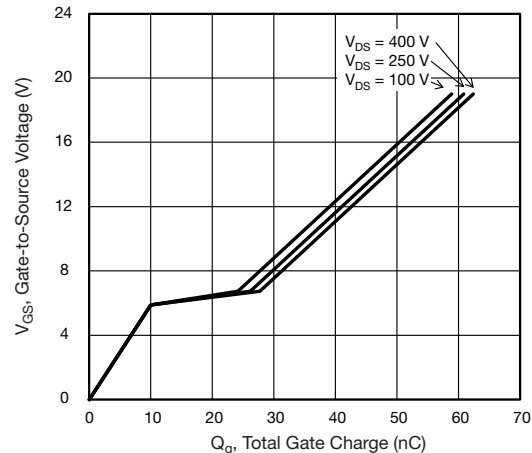
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	65	°C/W
Maximum junction-to-case (drain)	R_{thJC}	-	3.2	

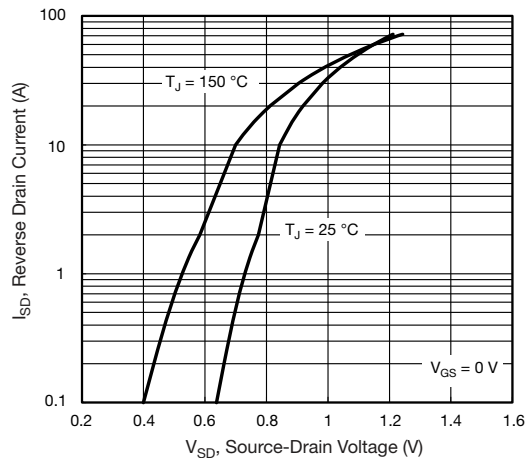
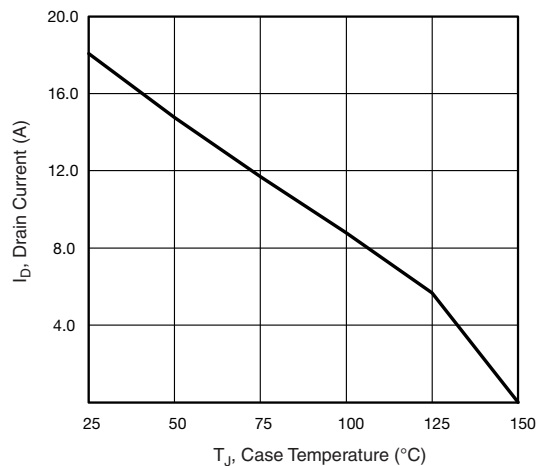
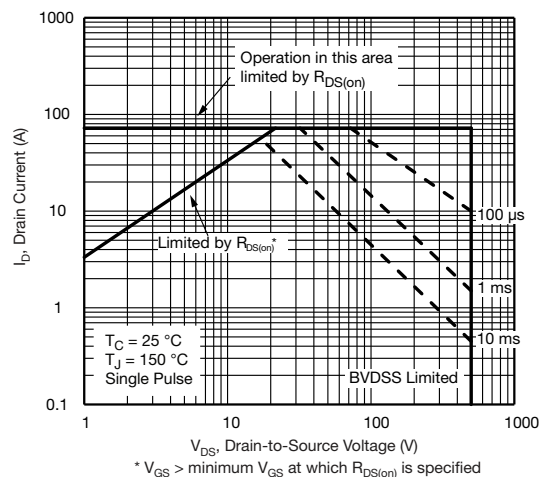
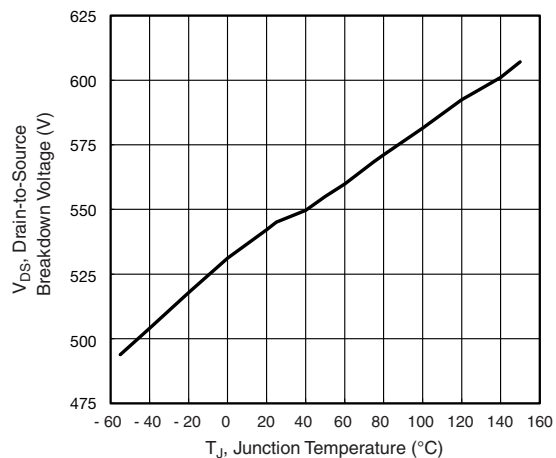
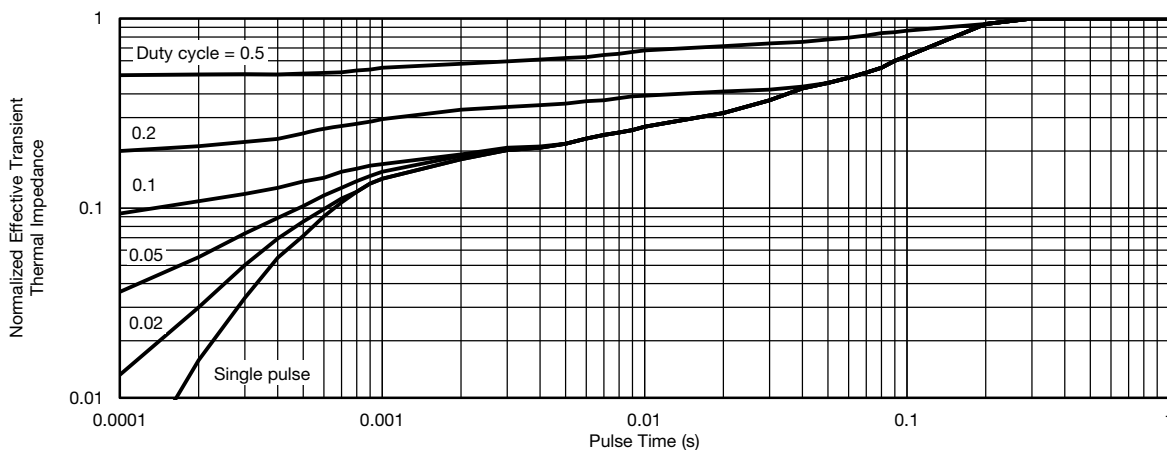
SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

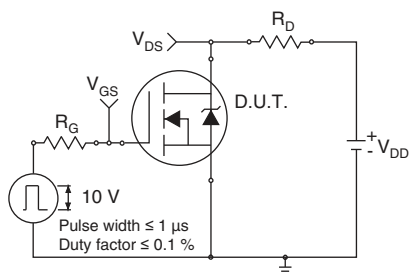
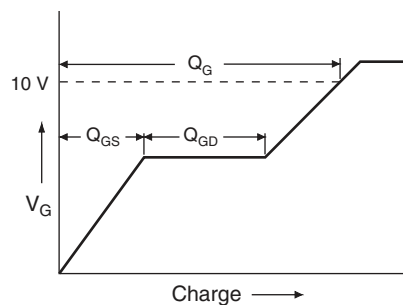
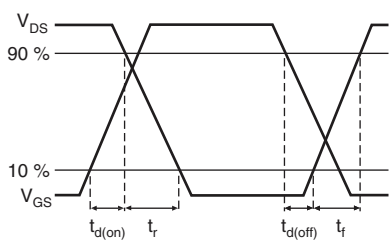
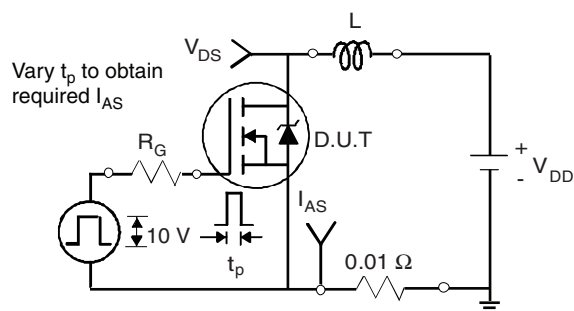
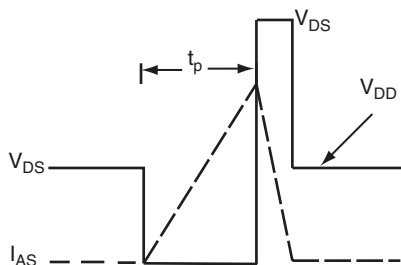
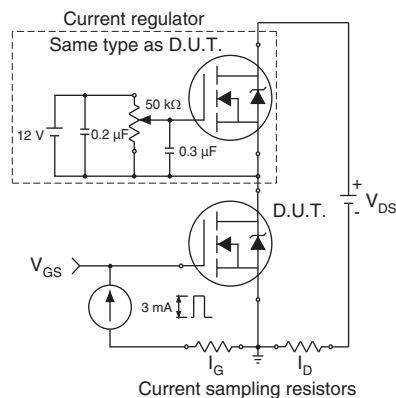
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	500	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^{\circ}\text{C}$, $I_D = 250\text{ }\mu\text{A}$	-	0.58	-	V/ $^{\circ}\text{C}$
Gate threshold voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	3.0	-	5.0	V
Gate-source leakage	I_{GSS}	$V_{GS} = \pm 30\text{ V}$	-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 500\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	1	μA
		$V_{DS} = 400\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	-	10	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 9\text{ A}$	-	0.23	0.28	Ω
Forward transconductance	g_{fs}	$V_{DS} = 50\text{ V}$, $I_D = 9\text{ A}$	-	6.4	-	S
Dynamic						
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 100\text{ V}$, $f = 1.0\text{ MHz}$	-	1500	-	pF
Output capacitance	C_{oss}		-	131	-	
Reverse transfer capacitance	C_{rss}		-	14	-	
Effective output capacitance, energy related ^a	$C_{o(er)}$	$V_{GS} = 0\text{ V}$, $V_{DS} = 0\text{ V to } 400\text{ V}$	-	113	-	
Effective output capacitance, time related ^b	$C_{o(tr)}$		-	164	-	
Total gate charge	Q_g	$V_{GS} = 10\text{ V}$, $I_D = 9\text{ A}$, $V_{DS} = 400\text{ V}$	-	38	76	nC
Gate-source charge	Q_{gs}		-	11	-	
Gate-drain charge	Q_{gd}		-	17	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 400\text{ V}$, $I_D = 9\text{ A}$, $V_{GS} = 10\text{ V}$, $R_g = 9.1\text{ }\Omega$	-	19	38	ns
Rise time	t_r		-	36	72	
Turn-off delay time	$t_{d(off)}$		-	36	72	
Fall time	t_f		-	30	60	
Gate input resistance	R_g	$f = 1\text{ MHz}$, open drain	-	1.7	-	Ω
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse P - N junction diode 	-	-	18	A
Pulsed diode forward current	I_{SM}		-	-	72	
Diode forward voltage	V_{SD}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_S = 9\text{ A}$, $V_{GS} = 0\text{ V}$	-	-	1.2	V
Reverse recovery time	t_{rr}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_F = I_S = 9\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_R = 20\text{ V}$	-	354	-	ns
Reverse recovery charge	Q_{rr}		-	3.9	-	μC
Reverse recovery current	I_{RRM}		-	21	-	A

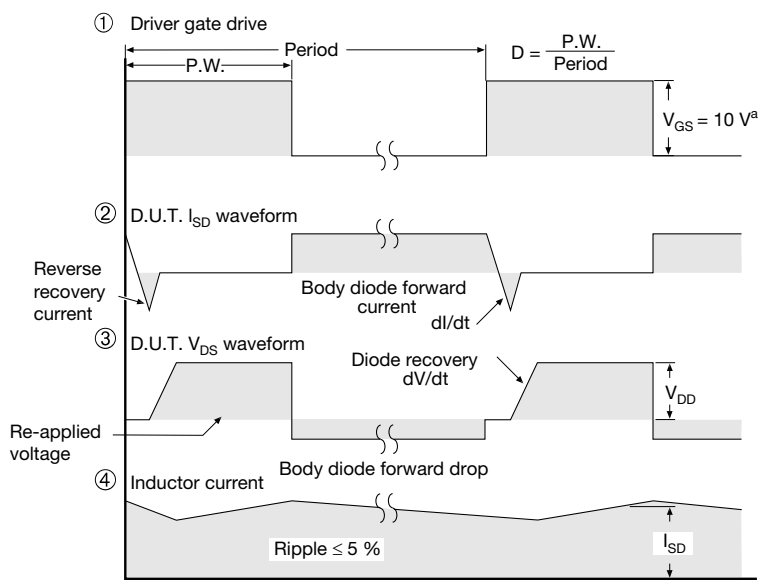
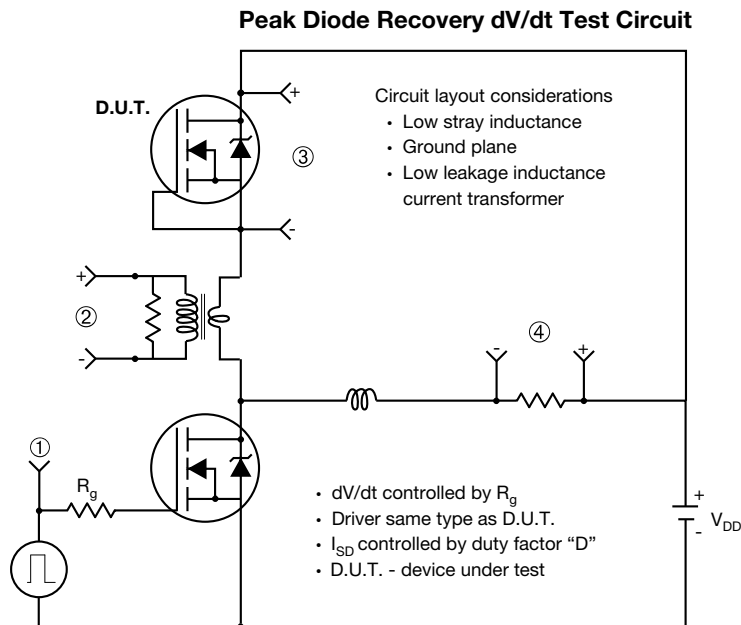
Notes

- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}
b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

Fig. 2 - Typical Output Characteristics

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 3 - Typical Transfer Characteristics

Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage


Fig. 7 - Typical Source-Drain Diode Forward Voltage

Fig. 9 - Maximum Drain Current vs. Case Temperature

Fig. 8 - Maximum Safe Operating Area

Fig. 10 - Typical Drain-to-Source Voltage vs. Temperature

Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case


Fig. 12 - Switching Time Test Circuit

Fig. 16 - Basic Gate Charge Waveform

Fig. 13 - Switching Time Waveforms

Fig. 14 - Unclamped Inductive Test Circuit

Fig. 15 - Unclamped Inductive Waveforms

Fig. 17 - Gate Charge Test Circuit


Note

a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 18 - For N-Channel

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TO-220 FULLPAK (High Voltage)

OPTION 1: FACILITY CODE = 9



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	4.60	4.70	4.80
b	0.70	0.80	0.91
b1	1.20	1.30	1.47
b2	1.10	1.20	1.30
C	0.45	0.50	0.63
D	15.80	15.87	15.97
e	2.54 BSC		
E	10.00	10.10	10.30
F	2.44	2.54	2.64
G	6.50	6.70	6.90
L	12.90	13.10	13.30
L1	3.13	3.23	3.33
Q	2.65	2.75	2.85
Q1	3.20	3.30	3.40
Ø R	3.08	3.18	3.28

Notes

1. To be used only for process drawing
2. These dimensions apply to all TO-220 FULLPAK leadframe versions 3 leads
3. All critical dimensions should C meet $C_{pk} > 1.33$
4. All dimensions include burrs and plating thickness
5. No chipping or package damage
6. Facility code will be the 1st character located at the 2nd row of the unit marking

**OPTION 2: FACILITY CODE = Y**

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.570	4.830	0.180	0.190
A1	2.570	2.830	0.101	0.111
A2	2.510	2.850	0.099	0.112
b	0.622	0.890	0.024	0.035
b2	1.229	1.400	0.048	0.055
b3	1.229	1.400	0.048	0.055
c	0.440	0.629	0.017	0.025
D	8.650	9.800	0.341	0.386
d1	15.88	16.120	0.622	0.635
d3	12.300	12.920	0.484	0.509
E	10.360	10.630	0.408	0.419
e	2.54 BSC		0.100 BSC	
L	13.200	13.730	0.520	0.541
L1	3.100	3.500	0.122	0.138
n	6.050	6.150	0.238	0.242
Ø P	3.050	3.450	0.120	0.136
u	2.400	2.500	0.094	0.098
V	0.400	0.500	0.016	0.020

ECN: E19-0180-Rev. D, 08-Apr-2019
DWG: 5972

Notes

1. To be used only for process drawing
2. These dimensions apply to all TO-220 FULLPAK leadframe versions 3 leads
3. All critical dimensions should C meet $C_{pk} > 1.33$
4. All dimensions include burrs and plating thickness
5. No chipping or package damage
6. Facility code will be the 1st character located at the 2nd row of the unit marking



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